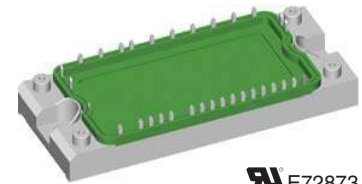
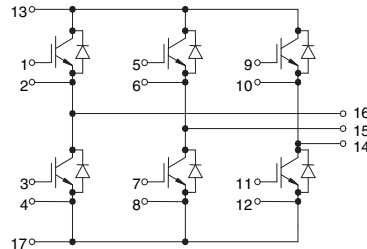


IGBT Modules

Sixpack

Short Circuit SOA Capability
Square RBSOA

I_{C25} = 62 A
 V_{CES} = 1200 V
 $V_{CE(sat)}$ typ. = 2.2 V



IXYS E72873

See outline drawing for pin arrangement

| IGBTs | | | |
|--|--|---|---------------|
| Symbol | Conditions | Maximum Ratings | |
| V_{CES} | $T_{VJ} = 25^{\circ}\text{C}$ to 150°C | 1200 | V |
| V_{GES} | | ± 20 | V |
| I_{C25} | $T_C = 25^{\circ}\text{C}$ | 62 | A |
| I_{C80} | $T_C = 80^{\circ}\text{C}$ | 44 | A |
| RBSOA | $V_{GE} = \pm 15\text{ V}$; $R_G = 39\ \Omega$; $T_{VJ} = 125^{\circ}\text{C}$ Clamped inductive load; $L = 100\ \mu\text{H}$ | $I_{CM} = 70$ $V_{CEK} \leq V_{CES}$ | A |
| t_{SC} (SCSOA) | $V_{CE} = V_{CES}$; $V_{GE} = \pm 15\text{ V}$; $R_G = 39\ \Omega$; $T_{VJ} = 125^{\circ}\text{C}$ non-repetitive | 10 | μs |
| P_{tot} | $T_C = 25^{\circ}\text{C}$ | 280 | W |

Features

- NPT IGBT technology
- low saturation voltage
- low switching losses
- switching frequency up to 30 kHz
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy parallelling
- MOS input, voltage controlled
- ultra fast free wheeling diodes
- solderable pins for PCB mounting
- package with copper base plate

Advantages

- space savings
- reduced protection circuits
- package designed for wave soldering

Typical Applications

- AC motor control
- AC servo and robot drives
- power supplies

| Symbol | Conditions | Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified) | | | |
|--|--|--|--------------------------------------|----------------------------------|-----|
| | | min. | typ. | max. | |
| $V_{CE(sat)}$ | $I_C = 35\text{ A}$; $V_{GE} = 15\text{ V}$; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$ | | 2.2 2.6 | 2.8 V | |
| $V_{GE(th)}$ | $I_C = 1.2\text{ mA}$; $V_{GE} = V_{CE}$ | 4.5 | | 6.5 V | |
| I_{CES} | $V_{CE} = V_{CES}$; $V_{GE} = 0\text{ V}$; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$ | | 2 | 2 mA mA | |
| I_{GES} | $V_{CE} = 0\text{ V}$; $V_{GE} = \pm 20\text{ V}$ | | | 200 nA | |
| $t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off} | Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 600\text{ V}$; $I_C = 35\text{ A}$ $V_{GE} = \pm 15\text{ V}$; $R_G = 39\ \Omega$ | | 100 80 500 70 5.4 4.2 | ns ns ns ns mJ mJ | |
| C_{ies} | | $V_{CE} = 25\text{ V}$; $V_{GE} = 0\text{ V}$; $f = 1\text{ MHz}$ | 2000 | pF | |
| Q_{Gon} | | $V_{CE} = 600\text{ V}$; $V_{GE} = 15\text{ V}$; $I_C = 35\text{ A}$ | 140 | nC | |
| R_{thJC} | | (per IGBT) | | 0.44 | K/W |

Diodes

| Symbol | Conditions | Maximum Ratings | |
|-----------|--------------------------|-----------------|---|
| I_{F25} | $T_C = 25^\circ\text{C}$ | 50 | A |
| I_{F80} | $T_C = 80^\circ\text{C}$ | 33 | A |

| Symbol | Conditions | Characteristic Values | | |
|----------------------|---|-----------------------|------|----------|
| | | min. | typ. | max. |
| V_F | $I_F = 35\text{ A}; V_{GE} = 0\text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$ | | 1.9 | 2.8 V |
| I_{RM} t_{tr} | $I_F = 35\text{ A}; di_F/dt = -400\text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}$ $V_R = 600\text{ V}; V_{GE} = 0\text{ V}$ | | 20 | A |
| | | | 200 | ns |
| R_{thJC} | (per diode) | | | 1.19 K/W |

Temperature Sensor NTC (MWI ... A7T version only)

| Symbol | Conditions | Characteristic Values | | |
|-------------------------|------------------------|-----------------------|-------------|--------------|
| | | min. | typ. | max. |
| R_{25} $B_{25/50}$ | $T = 25^\circ\text{C}$ | 4.75 | 5.0 3375 | 5.25 kΩ K |

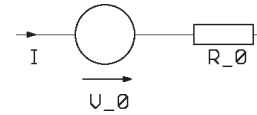
Module

| Symbol | Conditions | Maximum Ratings | |
|-----------------------|--|-----------------|------------------|
| T_{VJ} T_{stg} | | -40...+150 | $^\circ\text{C}$ |
| V_{ISOL} | $I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}$ | 2500 | V~ |
| M_d | Mounting torque (M5) | 2.7 - 3.3 | Nm |

| Symbol | Conditions | Characteristic Values | | |
|----------------|--|-----------------------|------|----------|
| | | min. | typ. | max. |
| $R_{pin-chip}$ | | | 5 | mΩ |
| d_S d_A | Creepage distance on surface Strike distance in air | 6 | | mm mm |
| R_{thCH} | with heatsink compound | | 0.02 | K/W |
| Weight | | | 180 | g |

Equivalent Circuits for Simulation

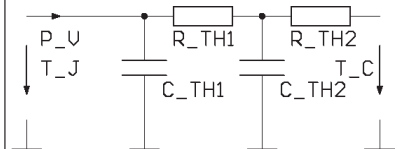
Conduction



IGBT (typ. at $V_{GE} = 15\text{ V}; T_J = 125^\circ\text{C}$)
 $V_0 = 1.6\text{ V}; R_0 = 28\text{ m}\Omega$

Free Wheeling Diode (typ. at $T_J = 125^\circ\text{C}$)
 $V_0 = 1.3\text{ V}; R_0 = 24.9\text{ m}\Omega$

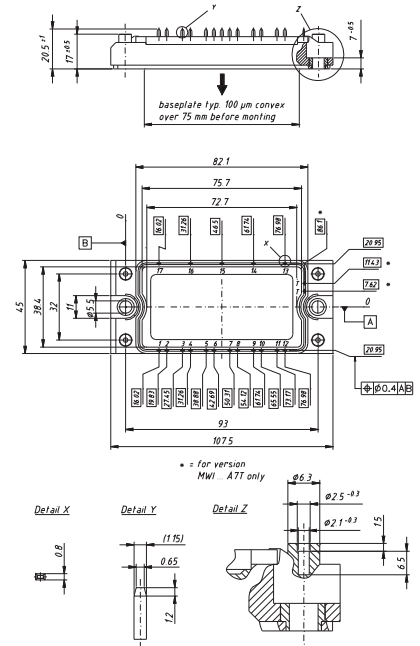
Thermal Response



IGBT (typ.)
 $C_{th1} = 0.166\text{ J/K}; R_{th1} = 0.342\text{ K/W}$
 $C_{th2} = 1.921\text{ J/K}; R_{th2} = 0.098\text{ K/W}$

Free Wheeling Diode (typ.)
 $C_{th1} = 0.081\text{ J/K}; R_{th1} = 0.973\text{ K/W}$
 $C_{th2} = 0.915\text{ J/K}; R_{th2} = 0.217\text{ K/W}$

Dimensions in mm (1 mm = 0.0394")



Higher magnification on page B3 - 72

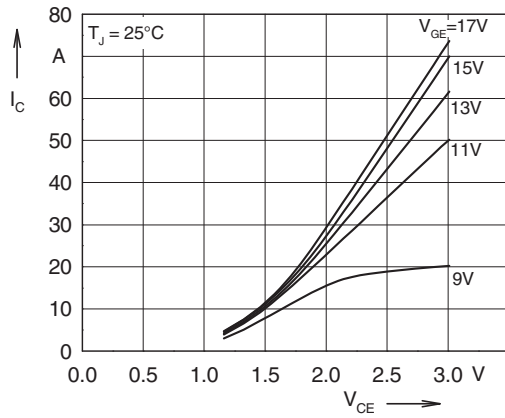


Fig. 1 Typ. output characteristics

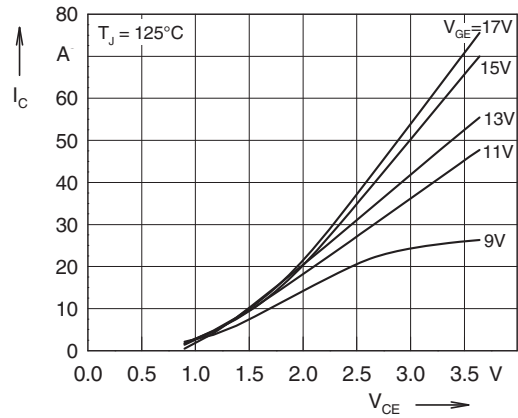


Fig. 2 Typ. output characteristics

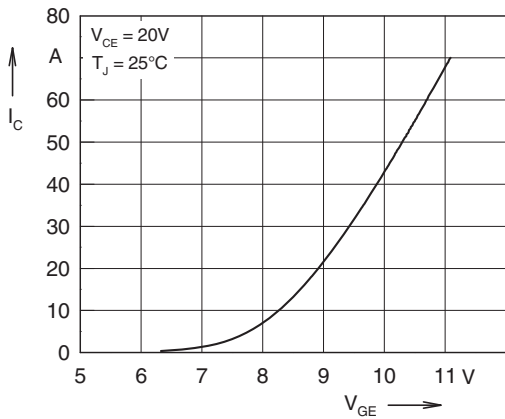


Fig. 3 Typ. transfer characteristics

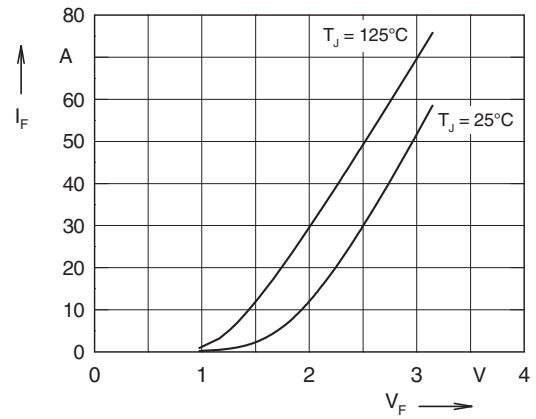


Fig. 4 Typ. forward characteristics of free wheeling diode

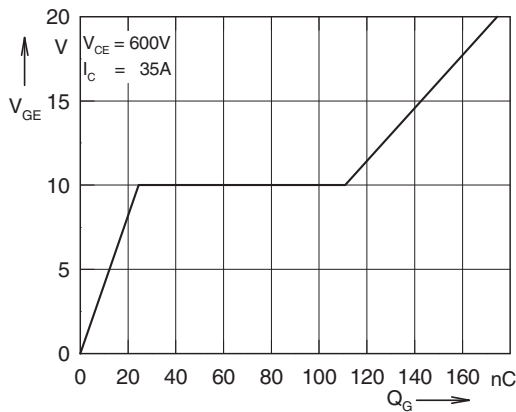


Fig. 5 Typ. turn on gate charge

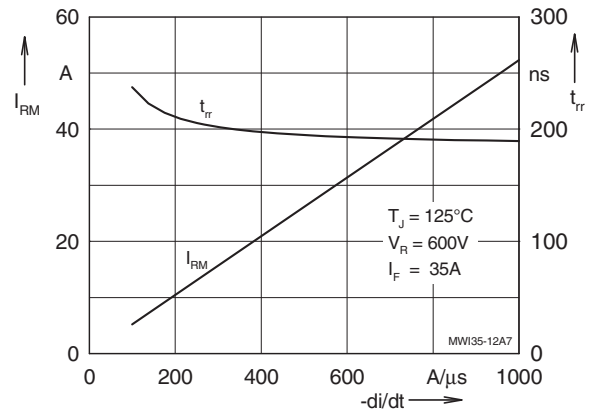


Fig. 6 Typ. turn off characteristics of free wheeling diode

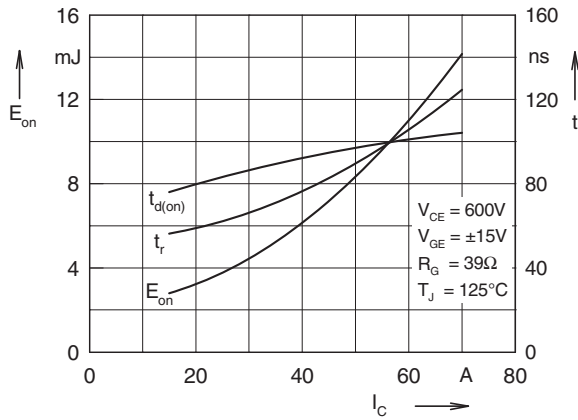


Fig. 7 Typ. turn on energy and switching times versus collector current

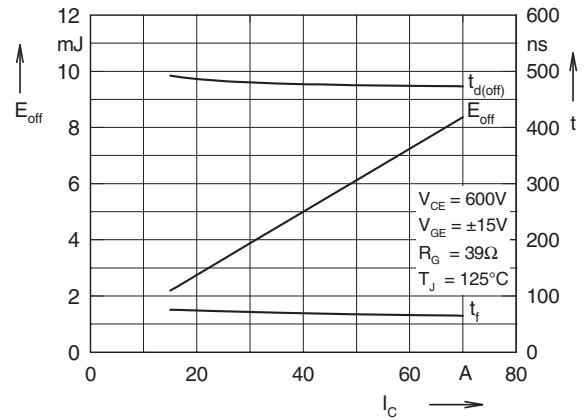


Fig. 8 Typ. turn off energy and switching times versus collector current

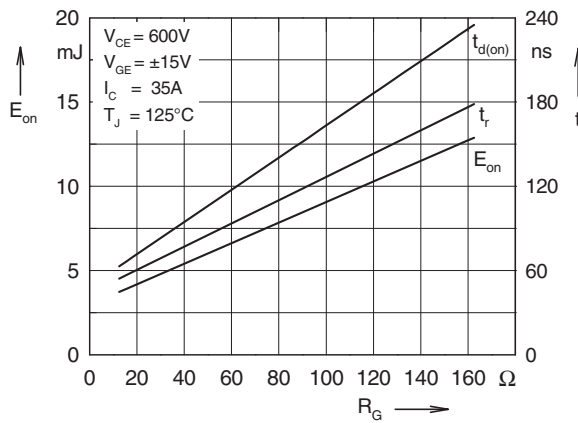


Fig. 9 Typ. turn on energy and switching times versus gate resistor

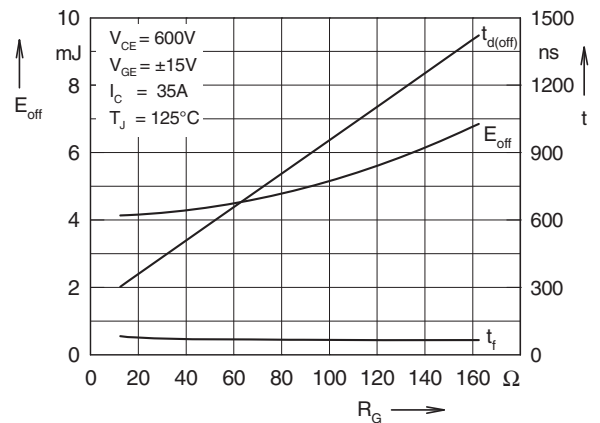


Fig.10 Typ. turn off energy and switching times versus gate resistor

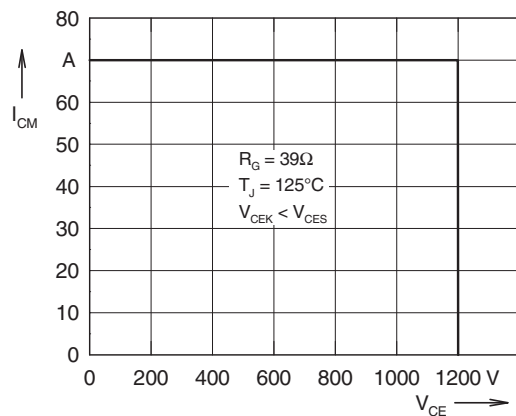


Fig. 11 Reverse biased safe operating area RBSOA

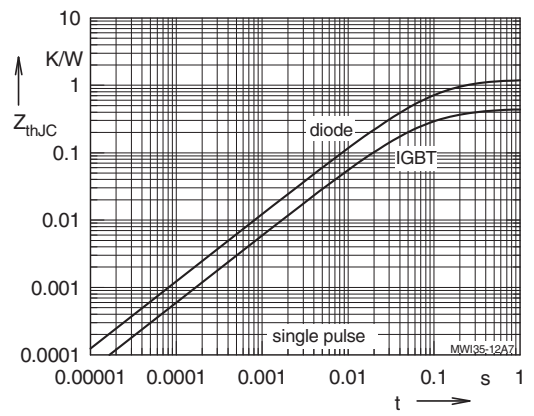


Fig. 12 Typ. transient thermal impedance